

IPL65R660E6AUMA1

IPL65R660E6AUMA1 Information

Heisener.com	 IPL65R660E6AUMA1 Infineon Technologies Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 4VSON 4-PowerTSFN For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPL65R660E6AUMA1 Specifications

Manufacturer Part Number	IPL65R660E6AUMA1
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	4-PowerTSFN
Series	CoolMOS? E6
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	650V
Current - Continuous Drain (Id) @ 25°C	7A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	3.5V @ 200µA
Gate Charge (Qg) (Max) @ Vgs	23nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	440pF @ 100V
Vgs (Max)	$\pm 20 V$
FET Feature	-
Power Dissipation (Max)	63W (Tc)
Rds On (Max) @ Id, Vgs	660 mOhm @ 2.1A, 10V
Operating Temperature	-40°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	Thin-Pak (8x8)
Package / Case	4-PowerTSFN
	Report errors?

IPL65R660E6AUMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IPL65R660E6AUMA1 Payment Methods



If you have any question about IPL65R660E6AUMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com